	ı	N THE UNITED STATES PAT	ENT AND TRADEMA	ARK OFFICE		
Applicants: Application No.: Date Filed: Title:		Marius K. Orlowski	Group Art Unit: Examiner:			
		METHOD FOR FORMING A SEMICONDUCTOR DEVICE HAVING A NOTCHED CONTROL ELECTRODE AND STRUCTURE THEREOF				
		INFORMATION DISCL	OSURE STATEMENT	Γ (IDS)		
	ssioner Fo Iria, VA	or Patents 22313				
SIR:						
States P for subr patent a	n attache atent and nitting a pplicatio	rdance with 37 C.F.R. §1.56 and in c d Form PTO/SB/08 and/or subsequent Trademark Office. Pursuant to the Copy of each cited U.S. patent and each stilled after June 30, 2003 and for a SC §371 after June 30, 2003, copies of	ntly identified herein, are Office waiving the requirer ch U.S. patent application all international application	for consideration by the United ment under 37 CFR 1.98 (a)(2)(i) publication for all U.S. national ns that have entered the national		
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b u § a	pefore the mailinder 37 C.F.R. (\$1.97(c)).	§1.311, or an action that otherw ement; therefore, charge deposit	Action under 37 C.F.R. §1.113, a Notice of Allowance ise closes prosecution in the application (See 37 C.F.R. account <b>502117</b> the fee set forth in 37 C.F.R. §1.17(p).
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Customer	DLA, INC. Number 23125		Respectfully submitted, Marius K. Orlowski  Kim-Marie Vo Agent for Applicant(s) Reg. No. 50,714 Tel. (512) 996-6839
Enclosure	s: 🗵	PTO/SB/08 References Foreign Search Report Other:	

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				Complete if Known		
				Application Number		
1	NFORMATION DISC	CLOSU	RE	Filing Date		
	STATEMENT BY APPLICANT			First Named Inventor	Marius K. Orlowski	
STATEMENT DI ALI EIGANT				Group Art Unit		
(use as many sheets as necessary)				Examiner Name		_
Sheet	1	of	1	Attorney Docket Number	SC13240TP	

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Examiner	Cite No. 1	Document Number	Publication Date	Name of Patentee or Applicant	Pages, Columns, Lines, Where Relevant
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